

# 2SD1632

## Silicon NPN Triple-Diffused Junction Mesa Type

### Horizontal Deflection Output

#### ■ Features

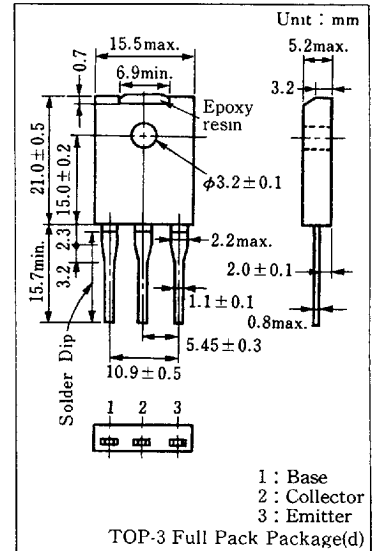
- Damper diode built-in
- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

#### ■ Absolute Maximum Ratings (Tc=25°C)

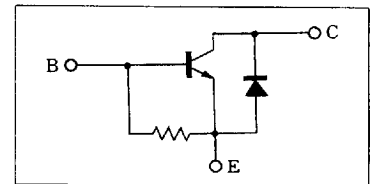
Item	Symbol	Value	Unit	
Collector-base voltage	$V_{CBO}$	1500	V	
Collector-emitter voltage	$V_{CES}$	1500	V	
Emitter-base voltage	$V_{EBO}$	5	V	
Collector current	$I_C$	4	A	
Peak collector current	$I_{CP}^*$	15	A	
Peak base current	$I_{BP}$	3.5	A	
Reverse peak base current	$I_{BP}$	-2.5	A	
Collector power dissipation	$P_C$	Tc=25°C	70	W
		Ta=25°C	3	
Junction temperature	$T_J$	130	°C	
Storage temperature	$T_{stg}$	-55 ~ +130	°C	

\* Non-repetitive peak value

#### ■ Package Dimensions



#### ■ Inner Circuit



#### ■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=750\text{ V}, I_E=0$			50	$\mu\text{A}$
		$V_{CB}=1500\text{ V}, I_E=0$			1	mA
Emitter-base voltage	$V_{EBO}$	$I_E=500\text{ mA}, I_C=0$	5			
DC current gain	$h_{FE}$	$V_{CE}=10\text{ V}, I_C=3\text{ A}$	5		15	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{ A}, I_B=1\text{ A}$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=3\text{ A}, I_B=1\text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=10\text{ V}, I_C=1\text{ A}, f=0.5\text{ MHz}$		2		MHz
Fall time	$t_f$	$I_C=3\text{ A}, I_{Bend}=1\text{ A}$			0.75	$\mu\text{s}$
Storage time	$t_{stg}$	$L_{leak}=5\mu\text{ H}$	4		9	$\mu\text{s}$
Diode forward voltage	$V_F$	$I_C=-4\text{ A}, I_B=0$			-2.2	V

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